TOSHIBA Transistor Silicon NPN Epitaxial Type

2SC5030

Strobe Flash Applications Medium Power Amplifier Applications

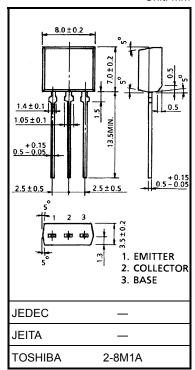
- High DC current gain : hFE (1) = 800 to 3200 (VCE = 2 V, IC = 0.5 A) : hFE (2) = 250 (min) (VCE = 2 V, IC = 4 A)
- Low saturation voltage: VCE (sat) = 0.5 V (max)

 $(I_{C} = 4 \text{ A}, I_{B} = 40 \text{ mA})$

• High collector power dissipation: $P_C = 1.3 \text{ W}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	50	V	
Collector-emitter voltage		V _{CES}	40	V	
		V _{CEO}	20		
Emitter-base voltage		V _{EBO}	8	V	
Collector current	DC	IC	5	A	
	Pulse (Note 1)	I _{CP}	8		
Base current		Ι _Β	0.5	А	
Collector power dissipation		P _C	1.3	W	
Junction temperature		Тj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Weight: 0.55 g (typ.)

Note 1: Conditions: Pulse width = 10 ms (max), duty cycle = 30% (max)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

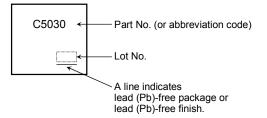
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm

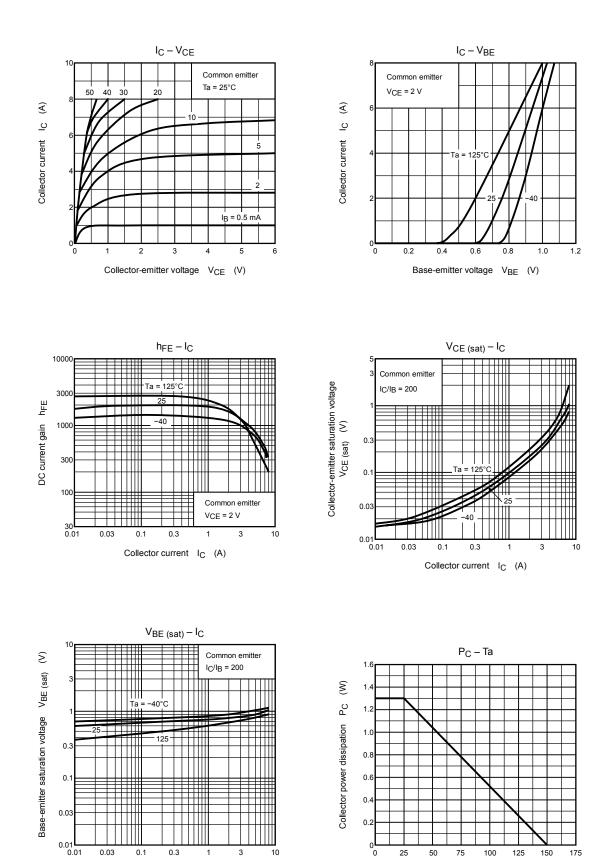
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 50 V, I _E = 0	_	_	100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 8 V, I _C = 0	_	_	100	nA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	20	—	—	V
DC current gain	h _{FE (1)}	V _{CE} = 2 V, I _C = 0.5 A	800	_	3200	
	h _{FE (2)}	V _{CE} = 2 V, I _C = 4 A	250	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 4 A, I _B = 40 mA	_	_	0.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 2 V, I _C = 4 A	_	_	1.2	V
Transition frequency	f _T	V _{CE} = 2 V, I _C = 0.5 A	_	150	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	-	45	—	pF

Marking

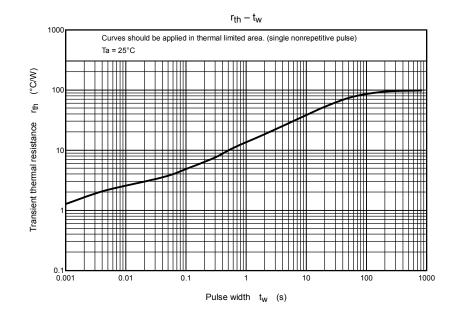


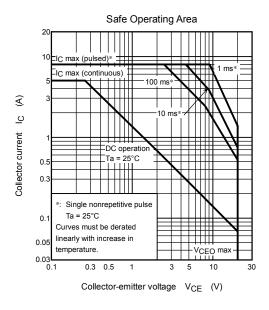
TOSHIBA



Ambient temperature Ta (°C)

Collector current I_C (A)





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